
APPLICATION DATA SHEET UNDER 37 C.F.R. §1.76

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Application Information**Title:****METHOD OF EPITAXY ON A SILICON SUBSTRATE
COMPRISING AREAS HEAVILY DOPED WITH ARSENIC**

Total Drawing Sheets:

4

Formal Drawings?

Yes

Application Type:

Non-Provisional Utility

Art Unit:

Unknown

Docket Number:

S1022/8562

Representative Information**Representative Customer Number::** 23628**Continuity Information**

This application is a:

Non-provisional

Claiming priority to:

Non-Provisional application docket nos. S1022/8562 and S1022/8072

Serial Number:

Not yet assigned

Filing Date:

July 10, 2001

Status:

Pending

Prior Foreign Applications

Foreign Application Number: 97/10032
Filing Date: July 31, 1997
Country: France
Priority Claimed: Yes

Assignee Information (when available)

Name of Assignee: STMicroelectronics S.A.
Address: 7, Avenue Gallieni, 94250 Gentilly, France

Docket 2000-2007-000668